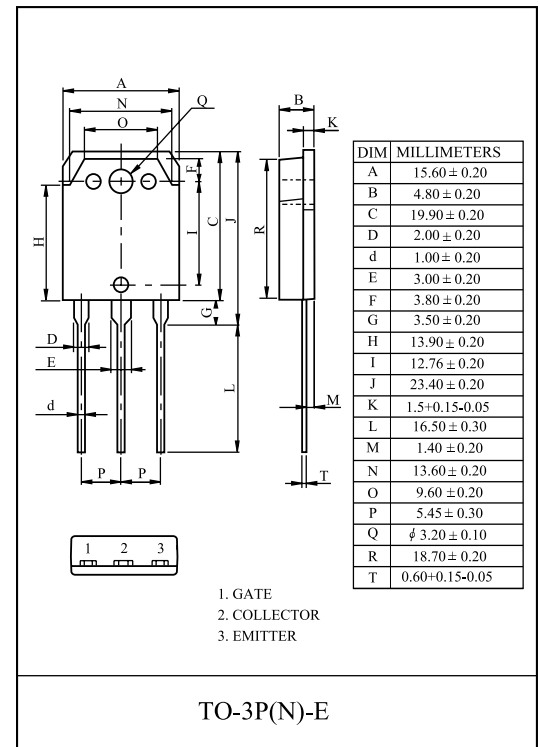


General Description

KEC NPT IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching application such as IH(induction heating), microwave oven, etc.

FEATURES

- High speed switching
- High ruggedness, temperature stable behavior
- Soft current turn-off waveforms
- Extremely enhanced avalanche capability



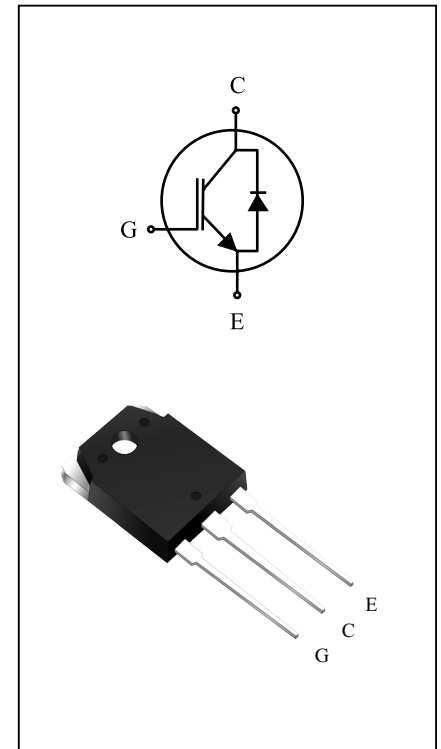
MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V _{CES}	1350	V
Gate-Emitter Voltage	V _{GES}	± 20	V
Collector Current	I _C	@Tc=25 °C	50 A
		@Tc=100 °C	25 A
Pulsed Collector Current	I _{CM} *	90	A
Diode Continuous Forward Current	I _F	25	A
Diode Maximum Forward Current	I _{FM}	150	A
Maximum Power Dissipation	P _D	@Tc=25 °C	220 W
		@Tc=100 °C	87 W
Maximum Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 to + 150	°C

*Repetitive rating : Pulse width limited by max. junction temperature

THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R _{thJC}	0.57	°C/W
Thermal Resistance, Junction to Case (DIODE)	R _{thJC}	2.0	°C/W
Thermal Resistance, Junction to Ambient	R _{thJA}	40	°C/W

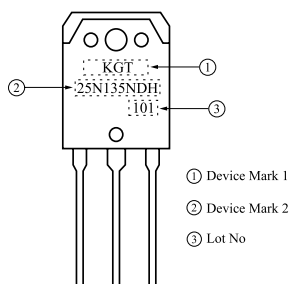


KGT25N135NDH

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Static							
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C=1mA$	1350	-	-	V	
Collector Cut-off Current	I_{CES}	$V_{GE}=0V, V_{CE}=1350V$	-	-	1.0	mA	
Gate Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	± 100	nA	
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=25mA$	4.5	6.0	7.5	V	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=25A$	-	1.85	2.25	V	
		$V_{GE}=15V, I_C=25A, T_C = 125^\circ C$	-	2.15	-	V	
		$V_{GE}=15V, I_C=50A$	-	2.40	-	V	
Dynamic							
Total Gate Charge	Q_g	$V_{CC}=600V, V_{GE}=15V, I_C=25A$	-	150	-	nC	
Gate-Emitter Charge	Q_{ge}		-	20	-	nC	
Gate-Collector Charge	Q_{gc}		-	70	-	nC	
Turn-On Delay Time	$t_{d(on)}$	$V_{CC}=600V, I_C=25A, V_{GE}=15V, R_G=10\Omega$ Inductive Load, $T_C = 25^\circ C$	-	40	-	ns	
Rise Time	t_r		-	25	-	ns	
Turn-Off Delay Time	$t_{d(off)}$		-	200	-	ns	
Fall Time	t_f		-	150	-	ns	
Turn-On Switching Loss	E_{on}		-	3.5	-	mJ	
Turn-Off Switching Loss	E_{off}		-	1.2	-	mJ	
Total Switching Loss	E_{ts}		-	4.7	-	mJ	
Turn-On Delay Time	$t_{d(on)}$		$V_{CC}=600V, I_C=25A, V_{GE}=15V, R_G=10\Omega$ Inductive Load, $T_C = 125^\circ C$	-	45	-	ns
Rise Time	t_r			-	30	-	ns
Turn-Off Delay Time	$t_{d(off)}$			-	210	-	ns
Fall Time	t_f	-		220	-	ns	
Turn-On Switching Loss	E_{on}	-		4.0	-	mJ	
Turn-Off Switching Loss	E_{off}	-		2.0	-	mJ	
Total Switching Loss	E_{ts}	-		6.0	-	mJ	
Input Capacitance	C_{ies}	$V_{CE}=30V, V_{GE}=0V, f=1MHz$	-	2500	-	pF	
Output Capacitance	C_{oes}		-	100	-	pF	
Reverse Transfer Capacitance	C_{res}		-	70	-	pF	

Marking



KGT25N135NDH

ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V_F	$I_F = 25A$	$T_C = 25^\circ C$	-	1.8	2.5	V
			$T_C = 125^\circ C$	-	1.9	-	
Diode Reverse Recovery Time	t_{rr}		$T_C = 25^\circ C$	-	270	350	ns
			$T_C = 125^\circ C$	-	300	-	
Diode Peak Reverse Recovery Current	I_{rr}	$I_F = 25A$ $di/dt = 200A/\mu s$	$T_C = 25^\circ C$	-	30	39	A
			$T_C = 125^\circ C$	-	31	-	
Diode Reverse Recovery Charge	Q_{rr}		$T_C = 25^\circ C$	-	3100	4700	nC
			$T_C = 125^\circ C$	-	4650	-	

KGT25N135NDH

Fig 1. Saturation Voltage Characteristics

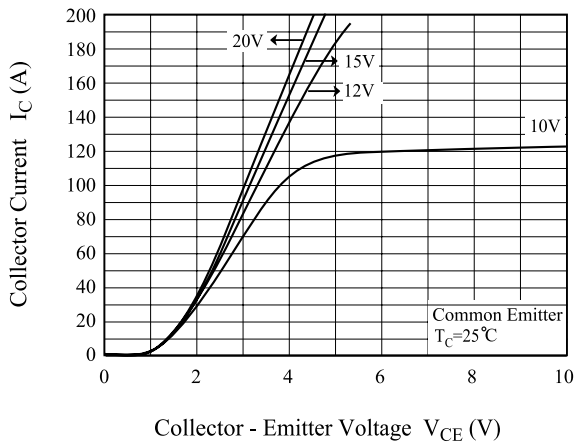


Fig 2. Saturation Voltage Characteristics

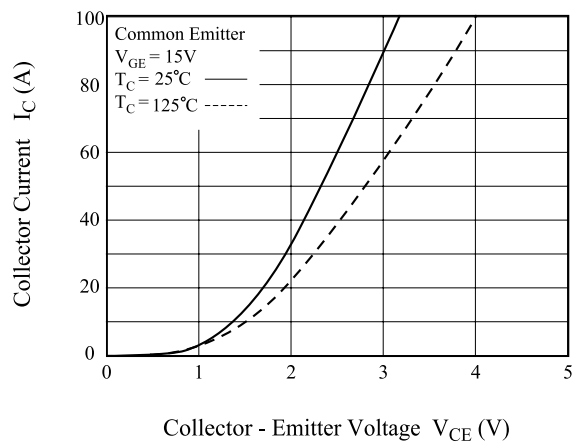


Fig 3. Saturation Voltage vs. Case Temperature

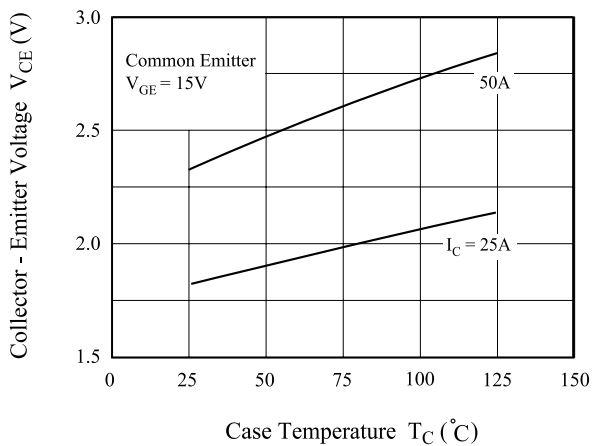


Fig 4. Saturation Voltage vs. V_{GE}

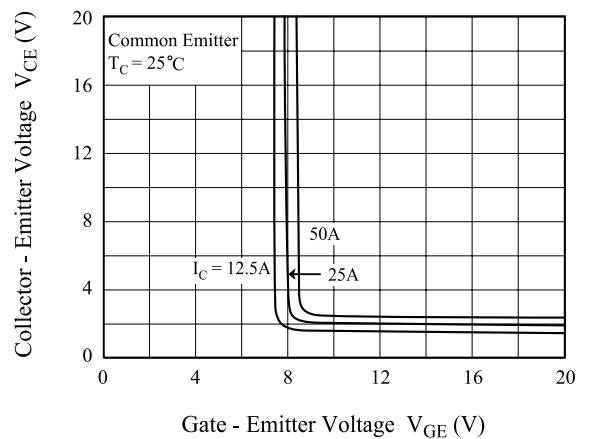


Fig 5. Saturation Voltage vs. V_{GE}

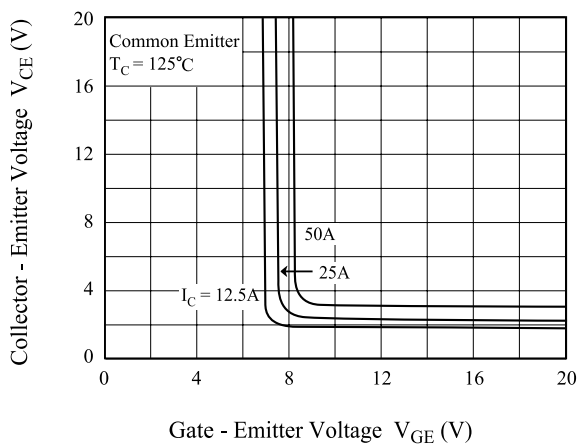
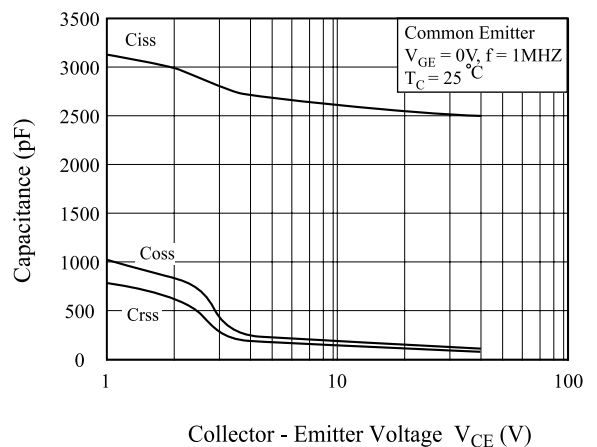


Fig 6. Capacitance Characteristics



KGT25N135NDH

Fig 7. Turn-On Characteristics vs. Gate Resistance

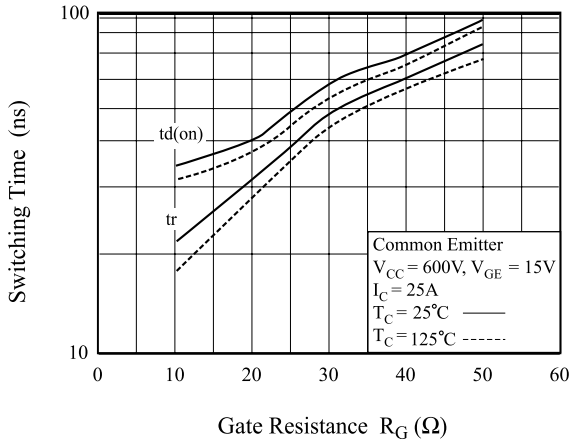


Fig 8. Turn-Off Characteristics vs. Gate Resistance

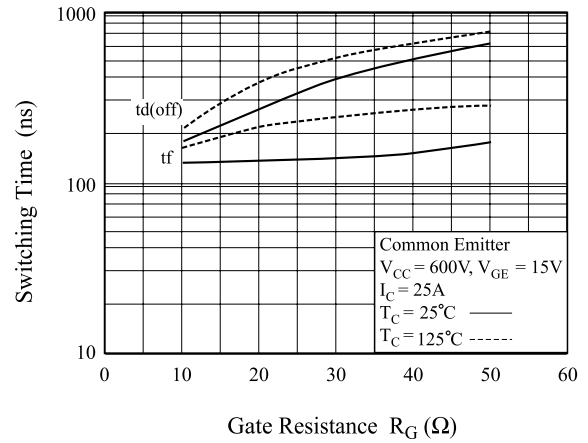


Fig 9. Switching Loss vs. Gate Resistance

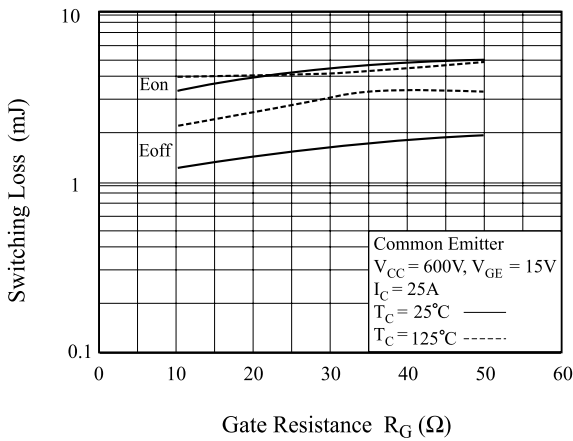


Fig 10. Turn-On Characteristics vs. Collector Current

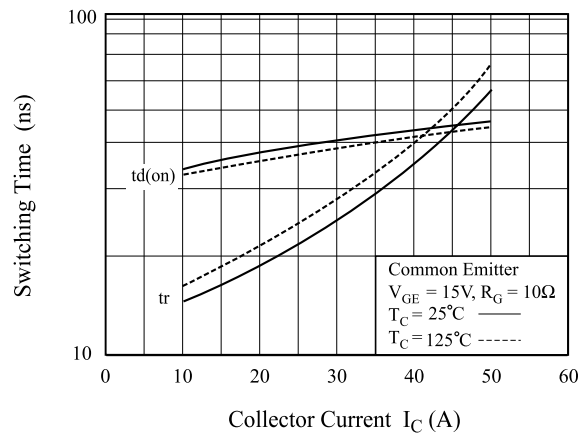


Fig 11. Turn-Off Characteristics vs. Collector Current

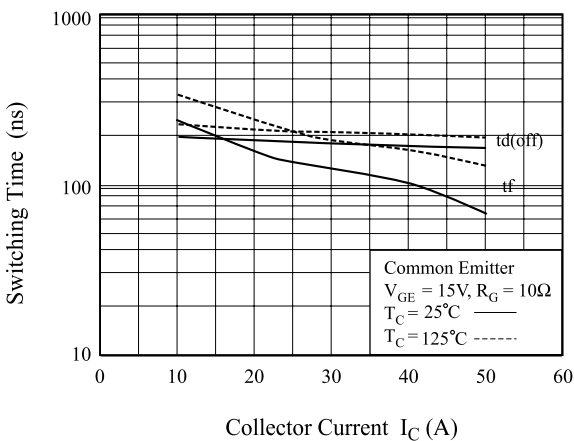
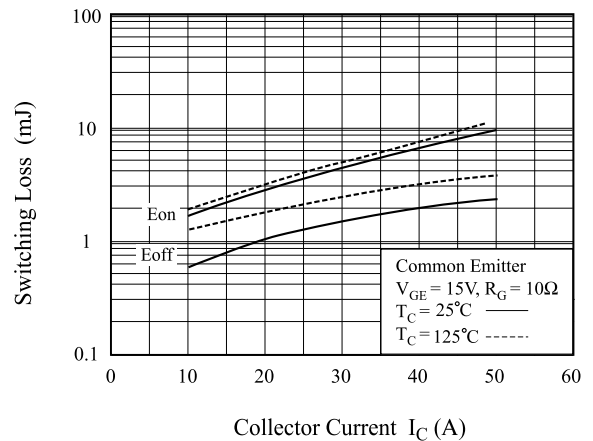


Fig 12. Switching Loss vs. Collector Current



KGT25N135NDH

Fig 13. Gate Charge Characteristics

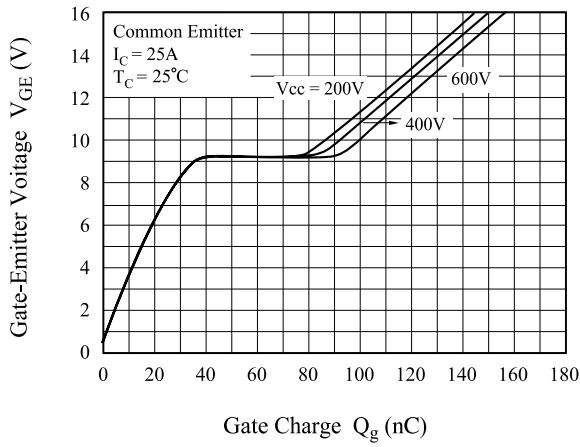


Fig 14. SOA Characteristics

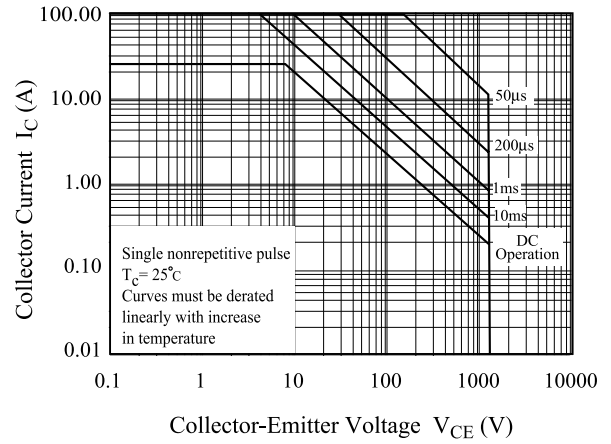


Fig 15. Turn-Off SOA

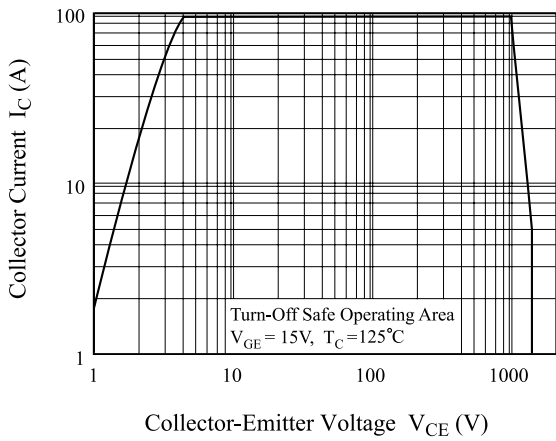
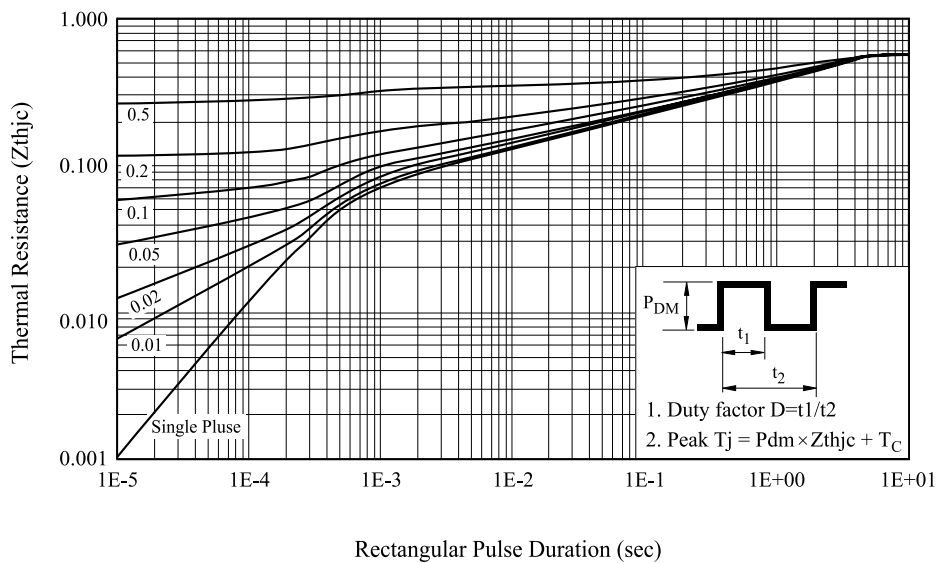


Fig 16. Transient Thermal Impedance of IGBT



KGT25N135NDH

Fig 17. Forward Characteristics

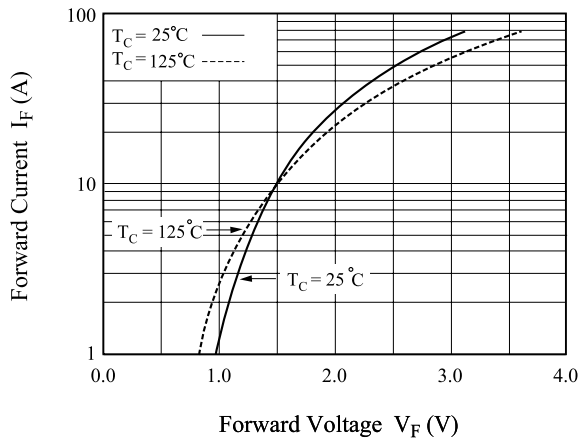


Fig 18. Reverse Recovery Current

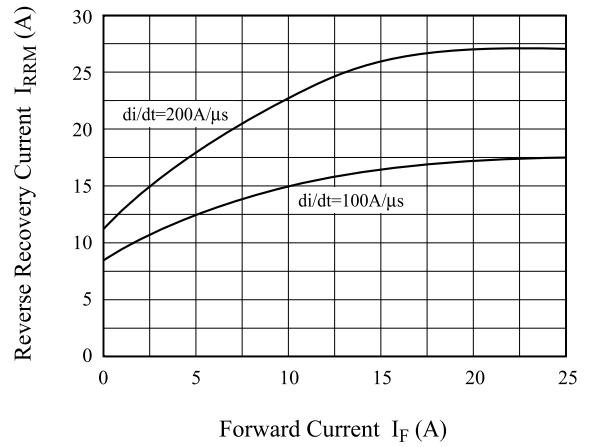
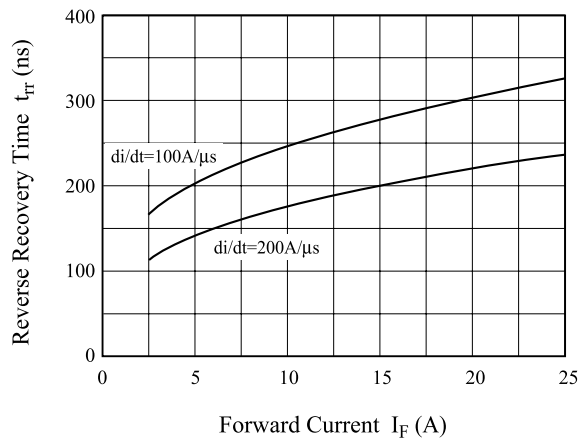


Fig 19. Reverse Recovery Time



KGT25N135NDH

Fig 21. Switching Test Circuit

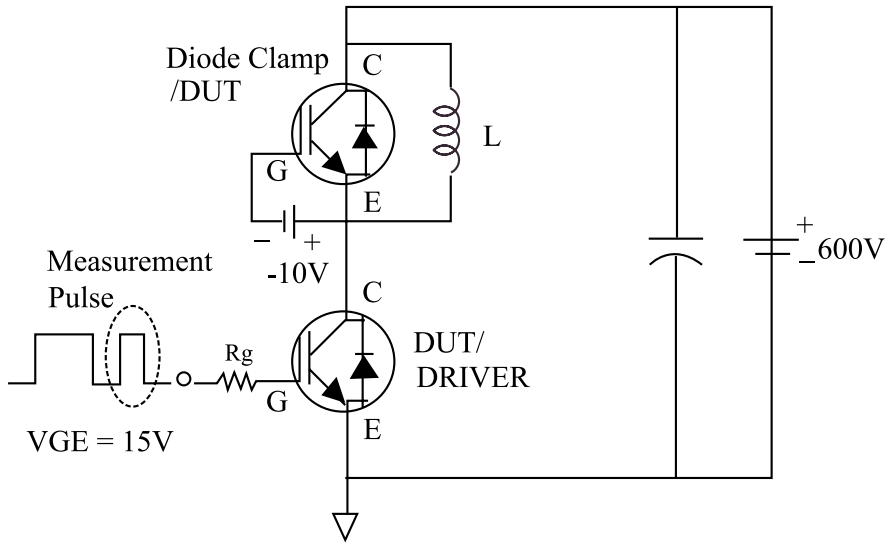


Fig 22. Definition Switching Time & Loss

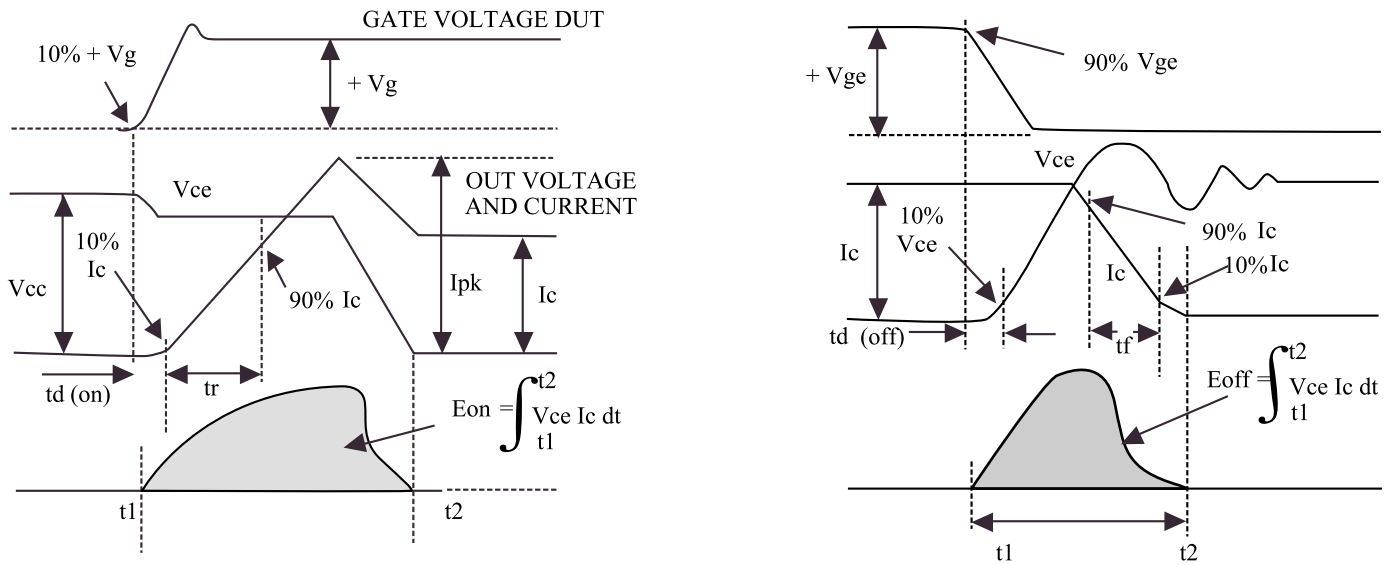


Fig 23. Definition Diode Switching Time

